

Vishay Semiconductors

PARAMETER	SYMBOL		VALUES	UNITS		
Maximum average on-state current	I _{T(AV)}		TEST CONDITIONS	8		
Maximum RMS on-state current	I _{T(RMS)}	T _C = 108 °C, 1	$T_C = 108 \text{ °C}, 180^\circ \text{ conduction, half sine wave}$			
Maximum peak one-cycle		10 ms sine pu	lse, rated V_{RRM} applied, T_{J} = 125 °C	95	A	
non-repetitive surge current	I _{TSM}	10 ms sine pu	lse, no voltage reapplied, $T_J = 125 \ ^{\circ}C$	110		
Maximum I ² t for fusing	l ² t	10 ms sine pu	lse, rated V_{RRM} applied, T_J = 125 °C	45	A ² s	
	141	10 ms sine pu	64	A-5		
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1 ms to 1	640	A²√s		
Maximum on-state voltage drop	V _{TM}	8 A, T _J = 25 °C	1.2	V		
On-state slope resistance	r _t	T.I = 125 °C		16.2	mΩ	
Threshold voltage	V _{T(TO)}	1J = 125 C		0.87	V	
Maximum reverse and direct leakage current	1/1	T _J = 25 °C	V _B = Rated V _{BBM} /V _{DBM}	0.05		
Maximum reverse and direct leakage current	I _{RM} /I _{DM}	T _J = 125 °C	VR - nated VRRM/ VDRM	1.0		
Typical holding current	Ι _Η	Anode supply T _J = 25 °C	30	mA		
Maximum latching current	١L	Anode supply	50			
Maximum rate of rise of off-state voltage	dV/dt	T _J = T _J max., I	150	V/µs		
Maximum rate of rise of turned-on current	dl/dt			100	A/µs	

TRIGGERING									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Maximum peak gate power	P _{GM}		8.0	W					
Maximum average gate power	P _{G(AV)}		2.0	vv					
Maximum peak positive gate current	+ I _{GM}		1.5	А					
Maximum peak negative gate voltage	- V _{GM}		10	V					
		Anode supply = 6 V, resistive load, T_J = - 65 °C	20						
Maximum required DC gate current to trigger	I _{GT}	Anode supply = 6 V, resistive load, T_J = 25 °C	15	mA					
		Anode supply = 6 V, resistive load, T_J = 125 °C	10						
		Anode supply = 6 V, resistive load, T_J = - 65 °C	1.2	V					
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \ ^{\circ}C$	1						
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	0.7	v					
Maximum DC gate voltage not to trigger	V _{GD}	T 105 °C V Dated value	0.2						
Maximum DC gate current not to trigger	I _{GD}	T _J = 125 °C, V _{DRM} = Rated value	0.1	mA					

SWITCHING									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Typical turn-on time	t _{gt}	T _J = 25 °C	0.8						
Typical reverse recovery time	t _{rr}	T.I = 125 °C	3	μs					
Typical turn-off time	tq	ij= 125 C	100						

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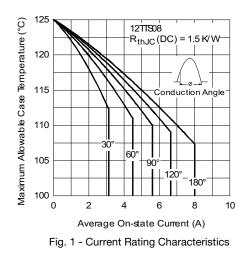
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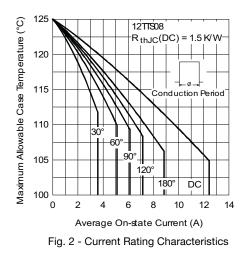
VS-12TTS08SPbF Series

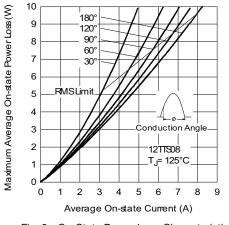


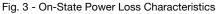
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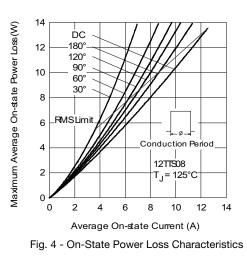
THERMAL AND MECHANICAL SPECIFICATIONS									
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum junction and storage temperature range		T _J , T _{Stg}		-40 to +125	°C				
Maximum thermal resistance, junction to case		R _{thJC}	DC operation	1.5					
Maximum thermal resistance, junction to ambient		R _{thJA}		62	°C/W				
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.5					
Approvimate weight				2	g				
Approximate weight				0.07	oz.				
Mounting torgue	minimum			6 (5)	kgf ⋅ cm				
Mounting torque —	maximum			12 (10)	(lbf · in)				
Marking device			Case style D ² PAK (SMD-220)	12TT:	S08S				











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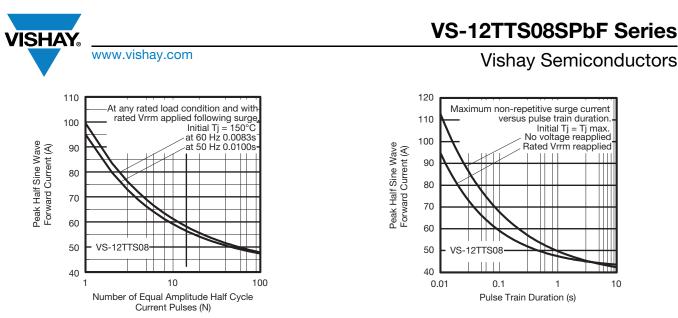
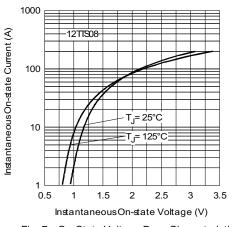
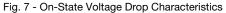


Fig. 5 - Maximum Non-Repetitive Surge Current

Fig. 6 - Maximum Non-Repetitive Surge Current





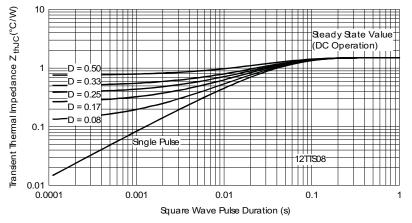


Fig. 8 - Thermal Impedance ZthJC Characteristics

VS-12TTS08SPbF Series

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ORDERING INFORMATION TABLE

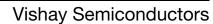
Device code	VS-	12	т	т	S	08	S	TRL	PbF
	1	2	3	4	5	6	7	8	9
	1 - 2 - 3 -	Cur	rent rati	niconduo ng (12.5 iguratior	A)	oduct			
	4 -	T = Pac	single tl kage: TO-220	nyristor					
	5 -	Тур	e of silio		ery recti	ifier			
	6 - 7 -		-	ng (08 = D ² PAK	-		rsion		
	8 -	• TF	-	be e and re be and re	-		-		
	9 -		-	(Pb)-fre		c onorite			

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-12TTS08SPbF	50	1000	Antistatic plastic tubes						
VS-12TTS08STRRPbF	800	800	13" diameter reel						
VS-12TTS08STRLPbF	800	800	13" diameter reel						

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95046					
Part marking information	www.vishay.com/doc?95054					
Packaging information	www.vishay.com/doc?95032					

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	www.vishay.com

Outline Dimensions

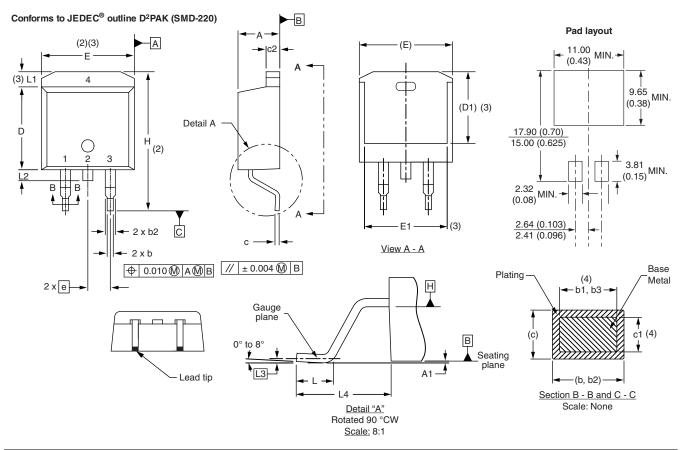


D²PAK

DIMENSIONS in millimeters and inches

www.vishay.com

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SYMBOL	MILLIM	IETERS	INC	HES	NOTES	NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		STWDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100) BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010) BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

(4) Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

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